

High speed switching series 5th generation

TRENCHSTOP™ 5 high speed switching IGBT copacked with full rated current RAPID 1 anti parallel diode

Features and Benefits:

High speed H5 technology offering

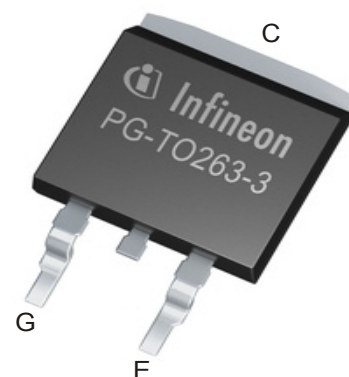
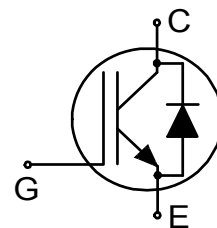
- Best-in-Class efficiency in hard switching and resonant topologies
- 650V breakdown voltage
- Low Q_G
- IGBT copacked with full rated current RAPID 1 fast antiparallel diode
- Maximum junction temperature 175°C
- Pb-free lead plating; RoHS compliant
- Complete product spectrum and PSpice Models:
<http://www.infineon.com/igbt/>

Potential Applications:

- Energy Generation
 - Solar String Inverter
 - Solar Micro Inverter
- Industrial Power Supplies
 - Industrial SMPS
 - Industrial UPS
- Metal Treatment
 - Welding
- Energy Distribution
 - Energy Storage
- Infrastructure – Charge
 - Charger

Product Validation:

Qualified for industrial applications according to the relevant tests of JEDEC47/20/22



Key Performance and Package Parameters

Type	V_{CE}	I_C	$V_{CEsat}, T_{vj}=25^{\circ}C$	T_{vjmax}	Marking	Package
IKB40N65EH5	650V	40A	1.65V	175°C	K40EEH5	PG-TO263-3



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Maximum Ratings

For optimum lifetime and reliability, Infineon recommends operating conditions that do not exceed 80% of the maximum ratings stated in this datasheet.

Parameter	Symbol	Value	Unit
Collector-emitter voltage, $T_{vj} \geq 25^{\circ}\text{C}$	V_{CE}	650	V
DC collector current, limited by T_{vjmax} $T_c = 25^{\circ}\text{C}$ $T_c = 100^{\circ}\text{C}$	I_C	74.0 46.0	A
Pulsed collector current, t_p limited by T_{vjmax}	I_{Cpuls}	160.0	A
Turn off safe operating area $V_{CE} \leq 650\text{V}$, $T_{vj} \leq 175^{\circ}\text{C}$, $t_p = 1\mu\text{s}$	-	160.0	A
Diode forward current, limited by T_{vjmax} ¹⁾ $T_c = 25^{\circ}\text{C}$ $T_c = 100^{\circ}\text{C}$	I_F	40.0 40.0	A
Diode pulsed current, t_p limited by T_{vjmax}	I_{Fpuls}	160.0	A
Gate-emitter voltage Transient Gate-emitter voltage ($t_p \leq 10\mu\text{s}$, $D < 0.010$)	V_{GE}	± 20 ± 30	V
Power dissipation $T_c = 25^{\circ}\text{C}$ Power dissipation $T_c = 100^{\circ}\text{C}$	P_{tot}	250.0 125.0	W
Operating junction temperature	T_{vj}	-40...+175	$^{\circ}\text{C}$
Storage temperature	T_{stg}	-55...+150	$^{\circ}\text{C}$
Soldering temperature, reflow soldering (MSL1 according to JEDEC J-STA-020)		260	$^{\circ}\text{C}$

Thermal Resistance

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
R _{th} Characteristics						
IGBT thermal resistance, junction - case	R _{th(j-c)}		-	-	0.60	K/W
Diode thermal resistance, junction - case	R _{th(j-c)}		-	-	0.75	K/W
Thermal resistance, min. footprint junction - ambient	R _{th(j-a)}		-	-	65	K/W
Thermal resistance, 6cm² Cu on PCB junction - ambient	R _{th(j-a)}		-	-	40	K/W

¹⁾ value limited by bondwire

High speed switching series 5th generationElectrical Characteristic, at $T_{vj} = 25^{\circ}\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Static Characteristic						
Collector-emitter breakdown voltage	$V_{(BR)CES}$	$V_{GE} = 0V, I_C = 0.20mA$	650	-	-	V
Collector-emitter saturation voltage	V_{CEsat}	$V_{GE} = 15.0V, I_C = 40.0A$ $T_{vj} = 25^{\circ}C$ $T_{vj} = 125^{\circ}C$ $T_{vj} = 175^{\circ}C$	- - -	1.65 1.85 1.95	2.10 - -	V
Diode forward voltage	V_F	$V_{GE} = 0V, I_F = 40.0A$ $T_{vj} = 25^{\circ}C$ $T_{vj} = 125^{\circ}C$ $T_{vj} = 175^{\circ}C$	- - -	1.45 1.42 1.39	1.70 - -	V
Gate-emitter threshold voltage	$V_{GE(th)}$	$I_C = 0.40mA, V_{CE} = V_{GE}$	3.2	4.0	4.8	V
Zero gate voltage collector current	I_{CES}	$V_{CE} = 650V, V_{GE} = 0V$ $T_{vj} = 25^{\circ}C$ $T_{vj} = 175^{\circ}C$	- -	- 2000	50 -	μA
Gate-emitter leakage current	I_{GES}	$V_{CE} = 0V, V_{GE} = 20V$	-	-	100	nA
Transconductance	g_{fs}	$V_{CE} = 20V, I_C = 40.0A$	-	50.0	-	S

Electrical Characteristic, at $T_{vj} = 25^{\circ}\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Dynamic Characteristic						
Input capacitance	C_{ies}	$V_{CE} = 25V, V_{GE} = 0V, f = 1MHz$	-	2500	-	pF
Output capacitance	C_{oes}		-	71	-	
Reverse transfer capacitance	C_{res}		-	9	-	
Gate charge	Q_G	$V_{CC} = 520V, I_C = 40.0A,$ $V_{GE} = 15V$	-	95.0	-	nC
Internal emitter inductance measured 5mm (0.197 in.) from case	L_E		-	7.0	-	nH

Switching Characteristic, Inductive Load

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
IGBT Characteristic, at $T_{vj} = 25^{\circ}\text{C}$						
Turn-on delay time	$t_{d(\text{on})}$	$T_{vj} = 25^{\circ}\text{C},$ $V_{CC} = 400\text{V}, I_C = 40.0\text{A},$ $V_{GE} = 0.0/15.0\text{V},$ $R_{G(\text{on})} = 15.0\Omega, R_{G(\text{off})} = 15.0\Omega,$ $L_{\sigma} = 30\text{nH}, C_{\sigma} = 31\text{pF}$ L_{σ}, C_{σ} from Fig. E Energy losses include “tail” and diode reverse recovery.	-	20	-	ns
Rise time	t_r		-	30	-	ns
Turn-off delay time	$t_{d(\text{off})}$		-	157	-	ns
Fall time	t_f		-	30	-	ns
Turn-on energy	E_{on}		-	1.10	-	mJ
Turn-off energy	E_{off}		-	0.40	-	mJ
Total switching energy	E_{ts}		-	1.50	-	mJ

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Turn-on delay time	$t_{d(on)}$	$T_{vj} = 25^{\circ}\text{C}$, $V_{CC} = 400\text{V}$, $I_C = 20.0\text{A}$, $V_{GE} = 0.0/15.0\text{V}$, $R_{G(on)} = 15.0\Omega$, $R_{G(off)} = 15.0\Omega$, $L\sigma = 30\text{nH}$, $C\sigma = 31\text{pF}$ $L\sigma$, $C\sigma$ from Fig. E Energy losses include "tail" and diode reverse recovery.	-	18	-	ns
Rise time	t_r		-	16	-	ns
Turn-off delay time	$t_{d(off)}$		-	160	-	ns
Fall time	t_f		-	30	-	ns
Turn-on energy	E_{on}		-	0.38	-	mJ
Turn-off energy	E_{off}		-	0.11	-	mJ
Total switching energy	E_{ts}		-	0.49	-	mJ

Diode Characteristic, at $T_{vj} = 25^{\circ}\text{C}$

Diode reverse recovery time	t_{rr}	$T_{vj} = 25^{\circ}\text{C}$, $V_R = 400\text{V}$, $I_F = 40.0\text{A}$, $di_F/dt = 1400\text{A}/\mu\text{s}$	-	78	-	ns
Diode reverse recovery charge	Q_{rr}		-	1.00	-	μC
Diode peak reverse recovery current	I_{rrm}		-	16.5	-	A
Diode peak rate of fall of reverse recovery current during t_b	di_{rr}/dt		-	-1500	-	A/ μs
Diode reverse recovery time	t_{rr}	$T_{vj} = 25^{\circ}\text{C}$, $V_R = 400\text{V}$, $I_F = 20.0\text{A}$, $di_F/dt = 1400\text{A}/\mu\text{s}$	-	56	-	ns
Diode reverse recovery charge	Q_{rr}		-	0.67	-	μC
Diode peak reverse recovery current	I_{rrm}		-	16.2	-	A
Diode peak rate of fall of reverse recovery current during t_b	di_{rr}/dt		-	-1324	-	A/ μs

Switching Characteristic, Inductive Load

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
IGBT Characteristic, at $T_{vj} = 150^{\circ}\text{C}$						
Turn-on delay time	$t_{d(on)}$	$T_{vj} = 150^{\circ}\text{C}$, $V_{CC} = 400\text{V}$, $I_C = 40.0\text{A}$, $V_{GE} = 0.0/15.0\text{V}$, $R_{G(on)} = 15.0\Omega$, $R_{G(off)} = 15.0\Omega$, $L\sigma = 30\text{nH}$, $C\sigma = 31\text{pF}$ $L\sigma$, $C\sigma$ from Fig. E Energy losses include “tail” and diode reverse recovery.	-	20	-	ns
Rise time	t_r		-	28	-	ns
Turn-off delay time	$t_{d(off)}$		-	175	-	ns
Fall time	t_f		-	30	-	ns
Turn-on energy	E_{on}		-	1.40	-	mJ
Turn-off energy	E_{off}		-	0.42	-	mJ
Total switching energy	E_{ts}		-	1.82	-	mJ
Turn-on delay time	$t_{d(on)}$	$T_{vj} = 150^{\circ}\text{C}$, $V_{CC} = 400\text{V}$, $I_C = 20.0\text{A}$, $V_{GE} = 0.0/15.0\text{V}$, $R_{G(on)} = 15.0\Omega$, $R_{G(off)} = 15.0\Omega$, $L\sigma = 30\text{nH}$, $C\sigma = 31\text{pF}$ $L\sigma$, $C\sigma$ from Fig. E Energy losses include “tail” and diode reverse recovery.	-	17	-	ns
Rise time	t_r		-	16	-	ns
Turn-off delay time	$t_{d(off)}$		-	180	-	ns
Fall time	t_f		-	26	-	ns
Turn-on energy	E_{on}		-	0.64	-	mJ
Turn-off energy	E_{off}		-	0.12	-	mJ
Total switching energy	E_{ts}		-	0.76	-	mJ

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Diode Characteristic, at $T_{vj} = 150^{\circ}\text{C}$

Diode reverse recovery time	t_{rr}	$T_{vj} = 150^{\circ}\text{C},$ $V_R = 400\text{V},$ $I_F = 40.0\text{A},$ $di_F/dt = 1400\text{A}/\mu\text{s}$	-	105	-	ns
Diode reverse recovery charge	Q_{rr}		-	2.15	-	μC
Diode peak reverse recovery current	I_{rrm}		-	28.0	-	A
Diode peak rate of fall of reverse recovery current during t_b	di_{rr}/dt		-	-1950	-	A/ μs
Diode reverse recovery time	t_{rr}	$T_{vj} = 150^{\circ}\text{C},$ $V_R = 400\text{V},$ $I_F = 20.0\text{A},$ $di_F/dt = 1400\text{A}/\mu\text{s}$	-	85	-	ns
Diode reverse recovery charge	Q_{rr}		-	1.50	-	μC
Diode peak reverse recovery current	I_{rrm}		-	24.0	-	A
Diode peak rate of fall of reverse recovery current during t_b	di_{rr}/dt		-	-1830	-	A/ μs

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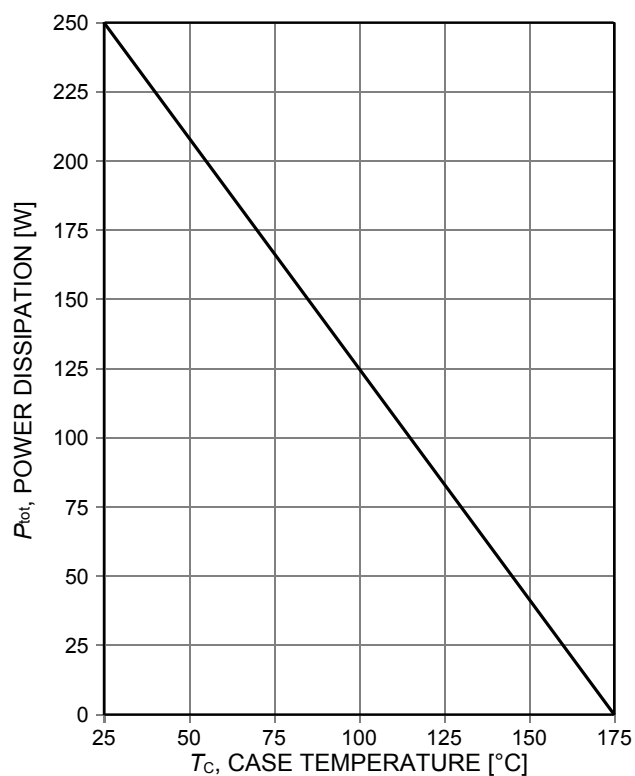


Figure 1. **Power dissipation as a function of case temperature**
($T_{vj} \leq 175^\circ\text{C}$)

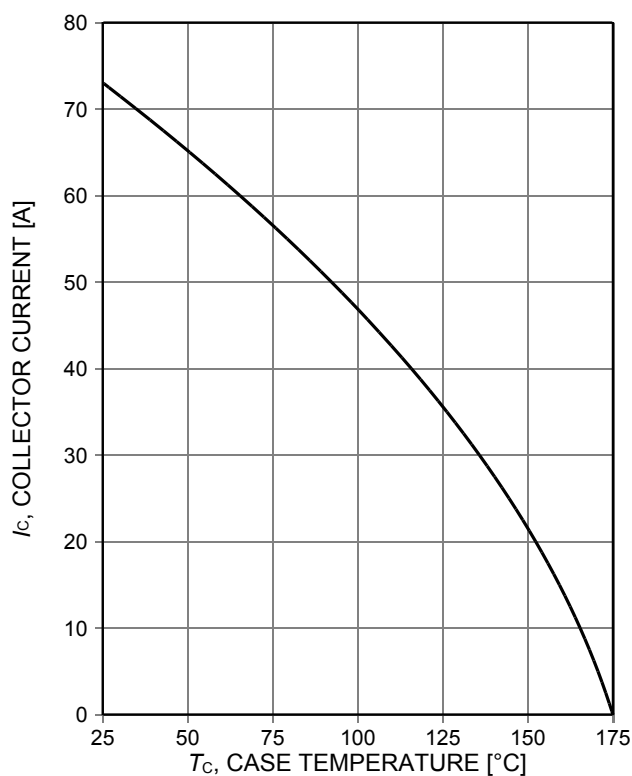


Figure 2. **Collector current as a function of case temperature**
($V_{GE} \geq 15\text{V}$, $T_{vj} \leq 175^\circ\text{C}$)

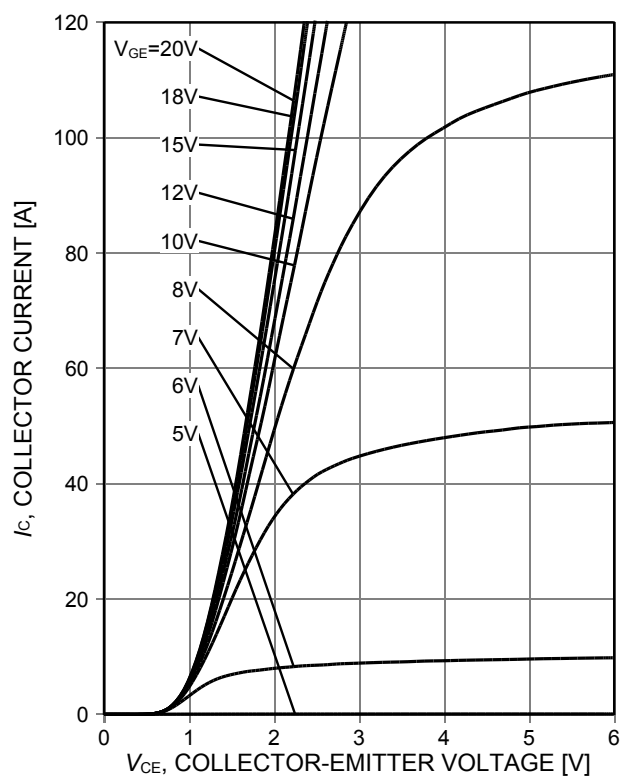


Figure 3. **Typical output characteristic**
($T_{vj} = 25^\circ\text{C}$)

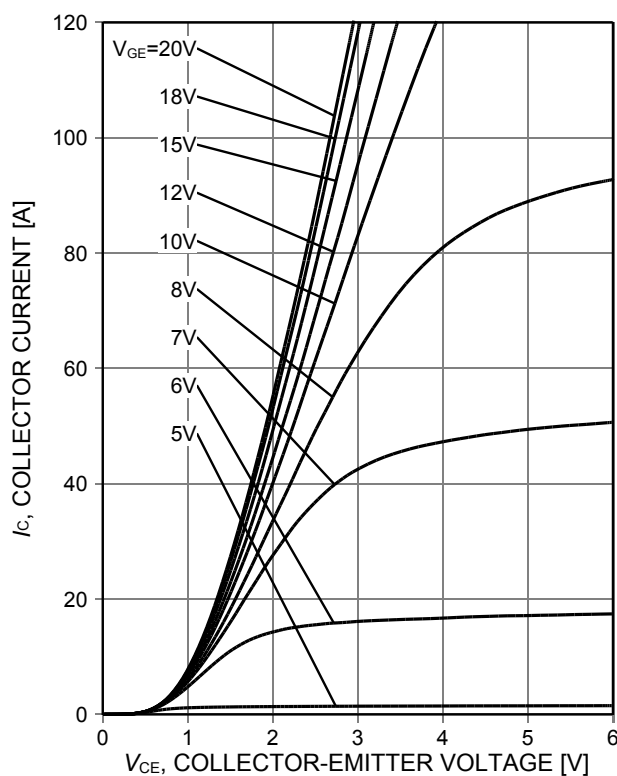


Figure 4. **Typical output characteristic**
($T_{vj} = 150^\circ\text{C}$)

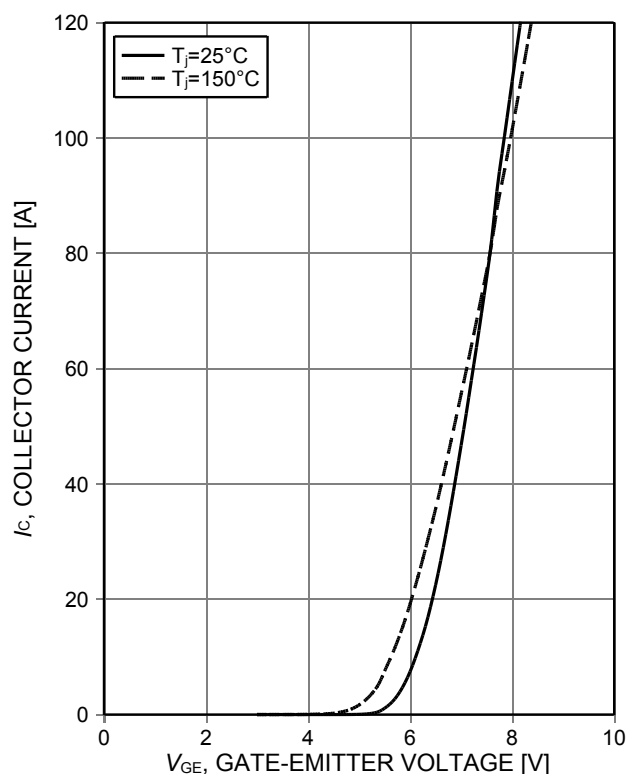


Figure 5. **Typical transfer characteristic**
($V_{CE}=20V$)

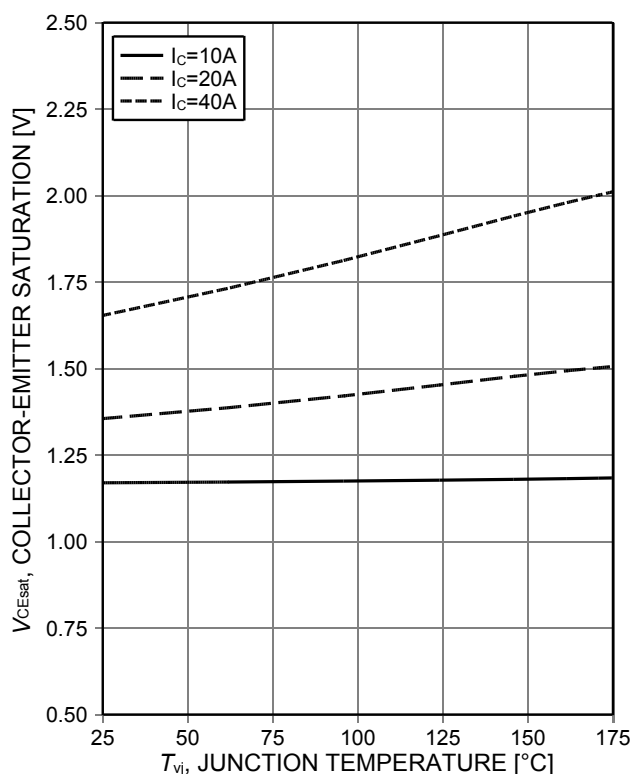


Figure 6. **Typical collector-emitter saturation voltage as a function of junction temperature**
($V_{GE}=15V$)

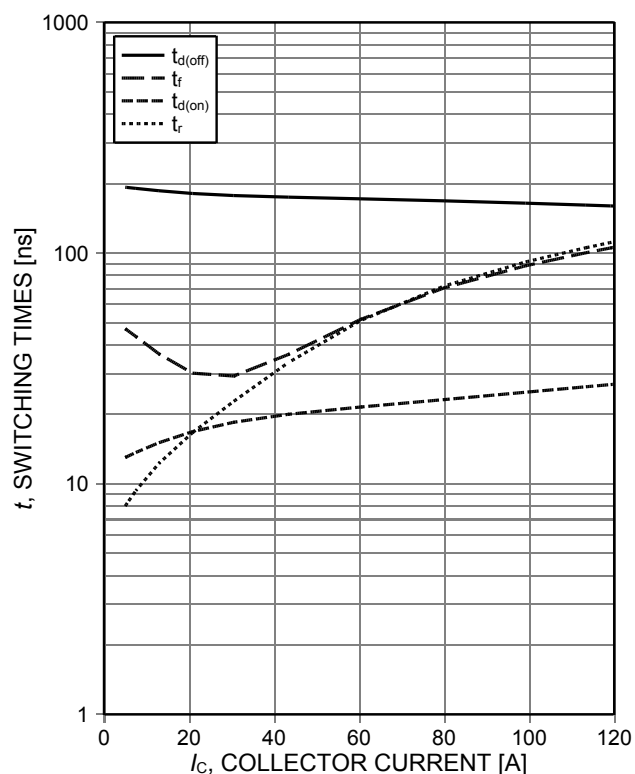


Figure 7. **Typical switching times as a function of collector current**
(inductive load, $T_{vj}=150^{\circ}C$, $V_{CE}=400V$, $V_{GE}=15/0V$, $R_G=15\Omega$, Dynamic test circuit in Figure E)

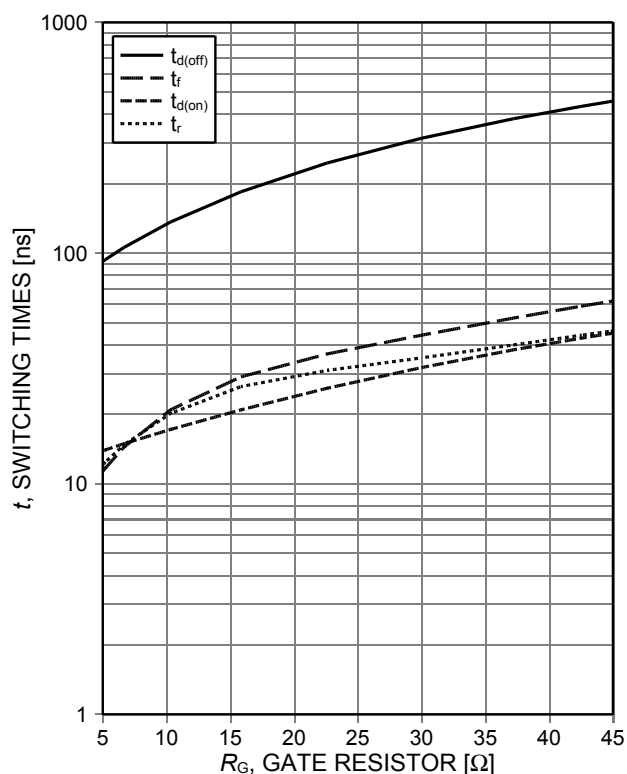


Figure 8. **Typical switching times as a function of gate resistor**
(inductive load, $T_{vj}=150^{\circ}C$, $V_{CE}=400V$, $V_{GE}=15/0V$, $I_C=40A$, Dynamic test circuit in Figure E)

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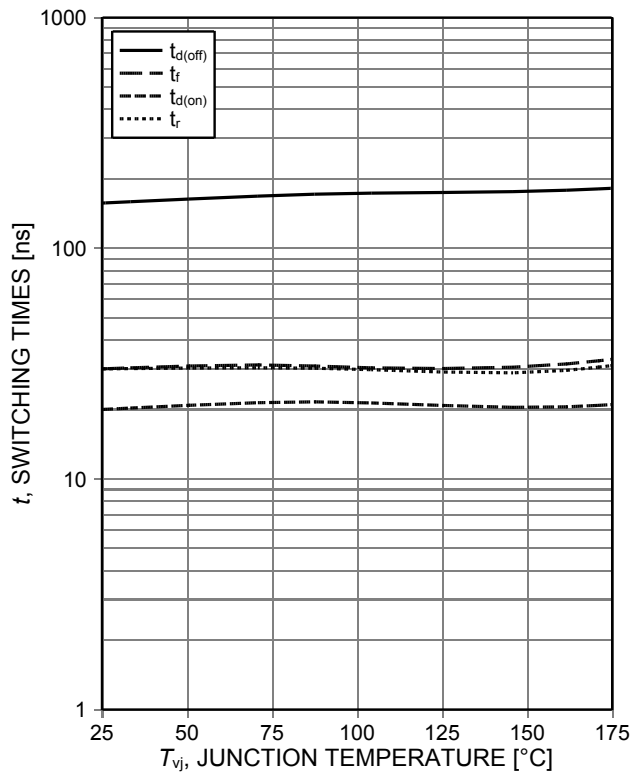


Figure 9. **Typical switching times as a function of junction temperature**
(inductive load, $V_{CE}=400V$, $V_{GE}=15/0V$, $I_C=40A$, $R_G=15\Omega$, Dynamic test circuit in Figure E)

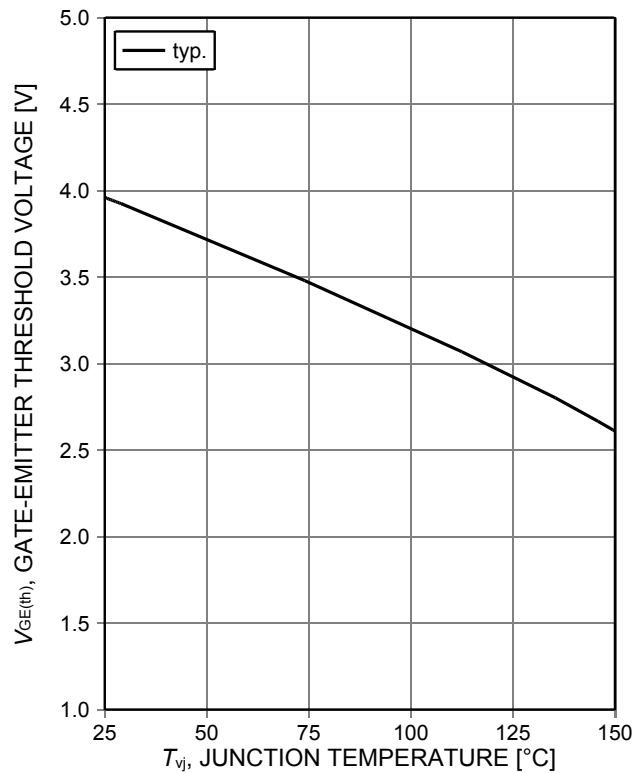


Figure 10. **Gate-emitter threshold voltage as a function of junction temperature**
($I_C=0.4mA$)

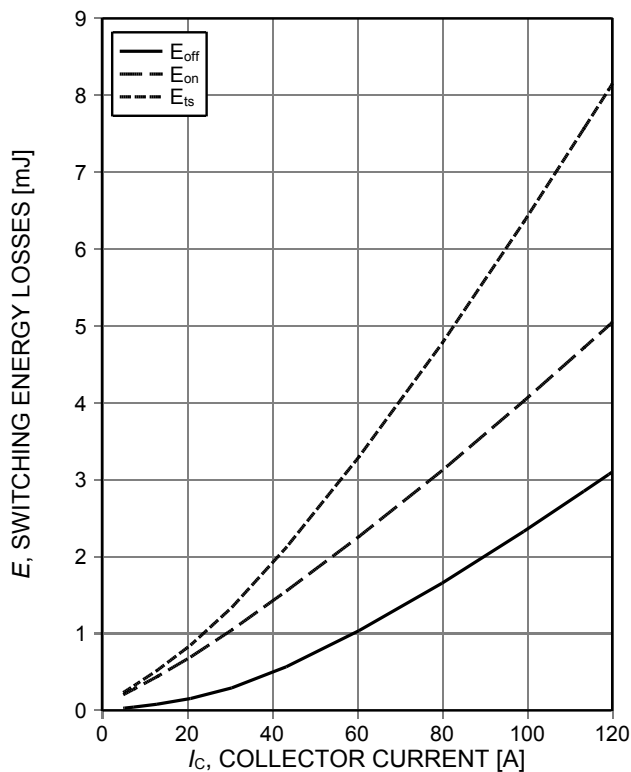


Figure 11. **Typical switching energy losses as a function of collector current**
(inductive load, $T_{vj}=150^\circ C$, $V_{CE}=400V$, $V_{GE}=15/0V$, $R_G=15\Omega$, Dynamic test circuit in Figure E)

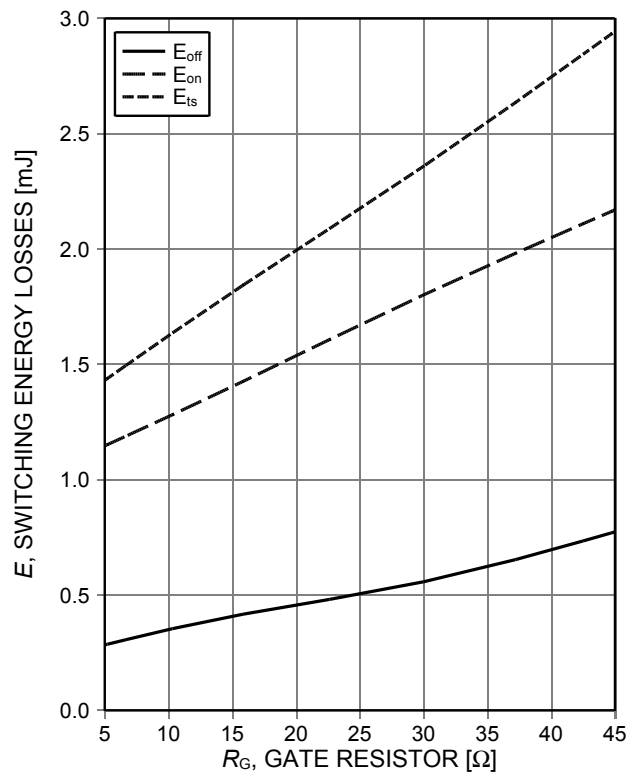


Figure 12. **Typical switching energy losses as a function of gate resistor**
(inductive load, $T_{vj}=150^\circ C$, $V_{CE}=400V$, $V_{GE}=15/0V$, $I_C=40A$, Dynamic test circuit in Figure E)

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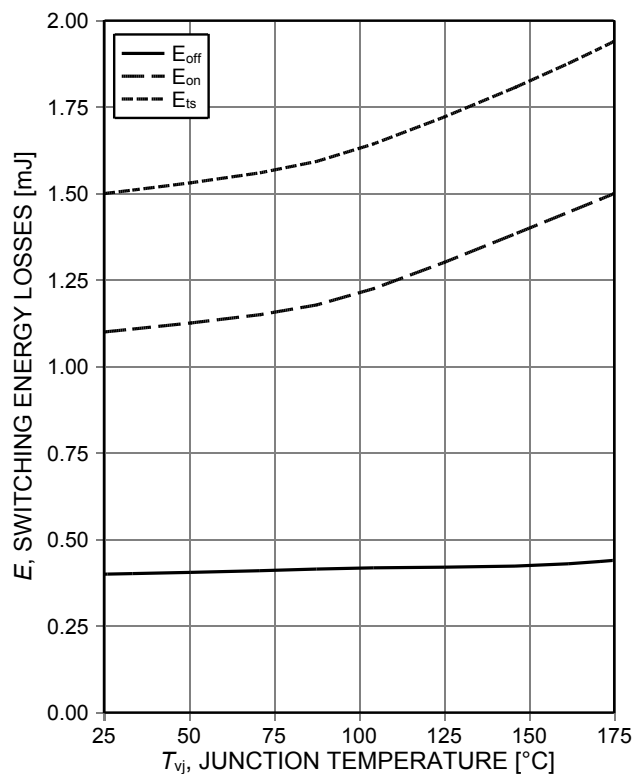


Figure 13. **Typical switching energy losses as a function of junction temperature**
(inductive load, $V_{CE}=400V$, $V_{GE}=15/0V$, $I_C=40A$, $R_G=15\Omega$, Dynamic test circuit in Figure E)

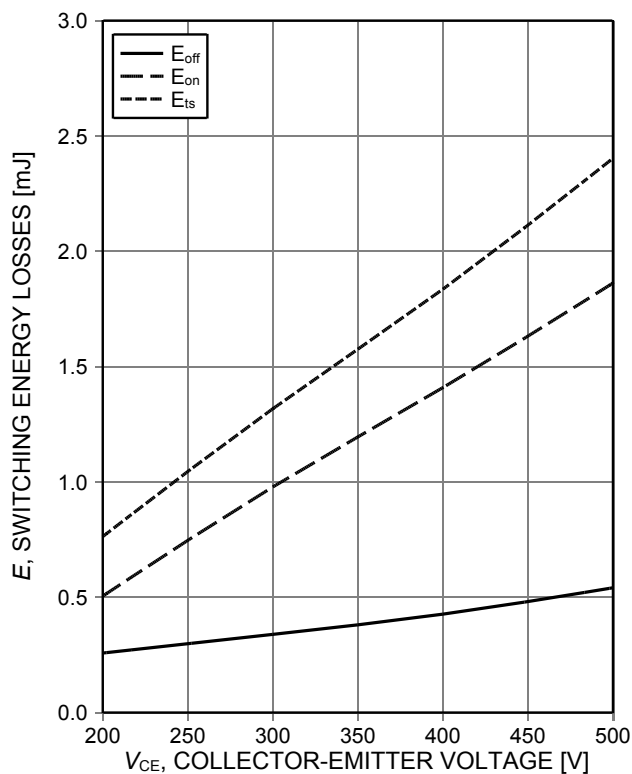


Figure 14. **Typical switching energy losses as a function of collector emitter voltage**
(inductive load, $T_{vj}=150^\circ C$, $V_{GE}=15/0V$, $I_C=40A$, $R_G=15\Omega$, Dynamic test circuit in Figure E)

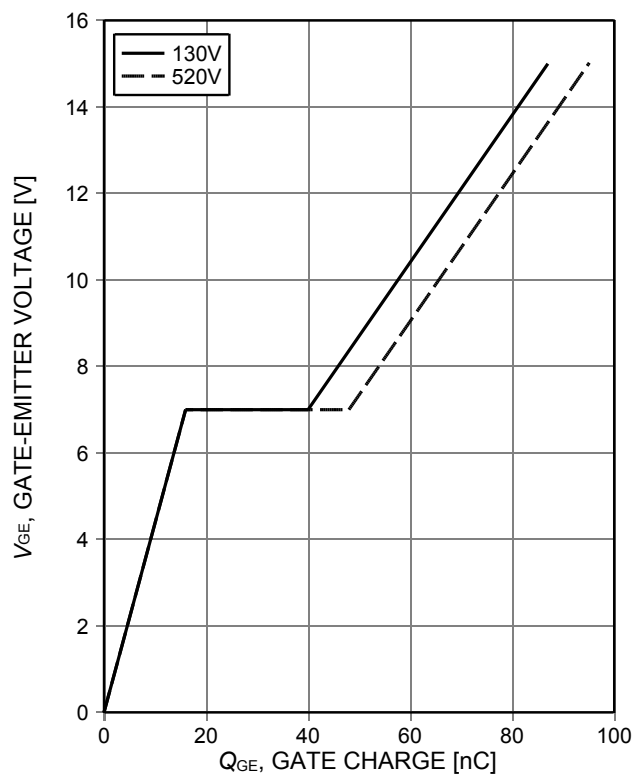


Figure 15. **Typical gate charge**
($I_C=40A$)

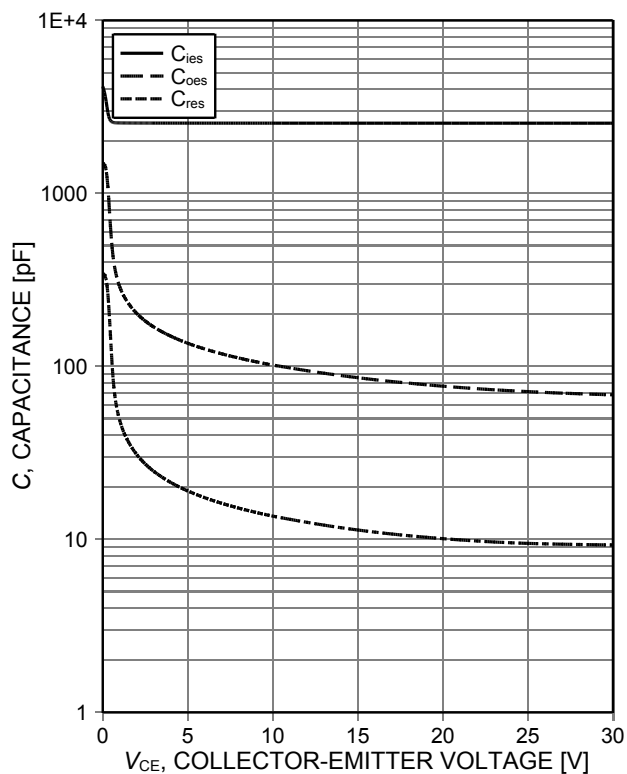


Figure 16. **Typical capacitance as a function of collector-emitter voltage**
($V_{GE}=0V$, $f=1MHz$)

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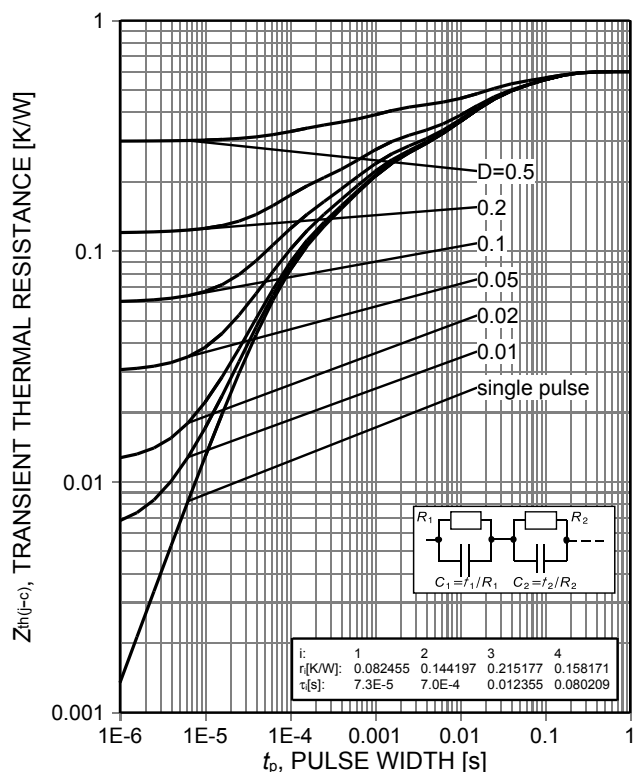


Figure 17. IGBT transient thermal resistance ($D=t_p/T$)

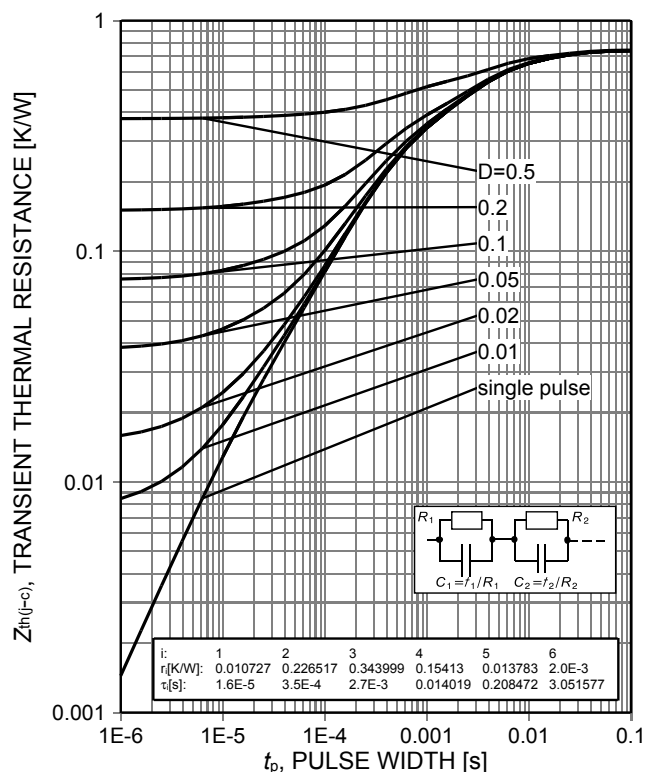


Figure 18. Diode transient thermal impedance as a function of pulse width ($D=t_p/T$)

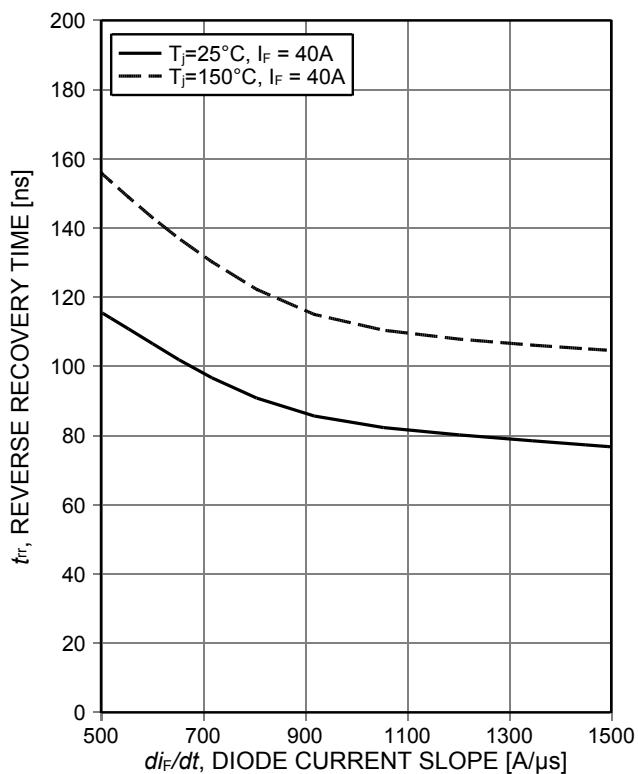


Figure 19. Typical reverse recovery time as a function of diode current slope ($V_R=400V$)

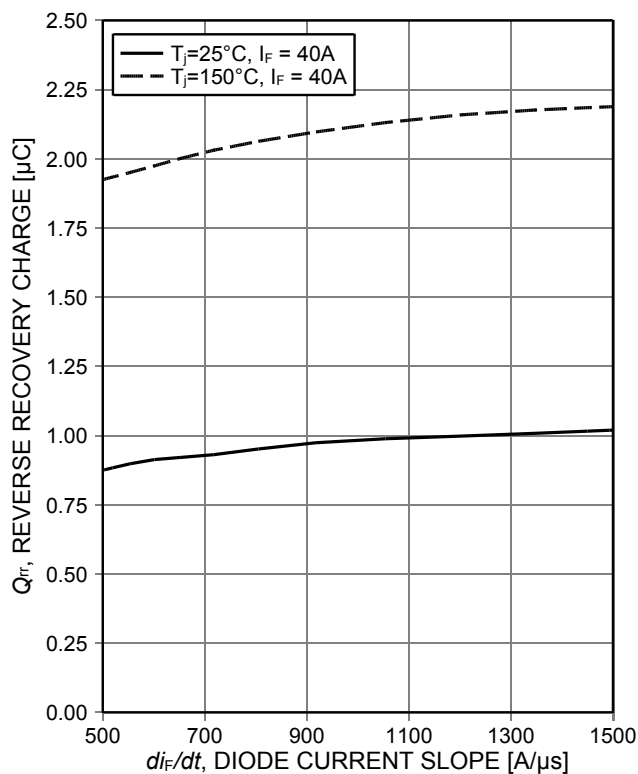


Figure 20. Typical reverse recovery charge as a function of diode current slope ($V_R=400V$)

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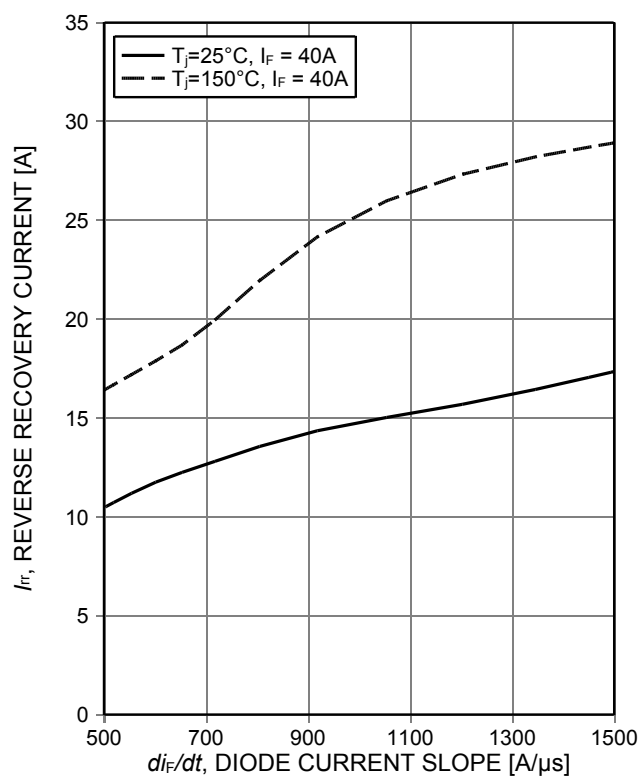


Figure 21. Typical reverse recovery current as a function of diode current slope ($V_R=400V$)

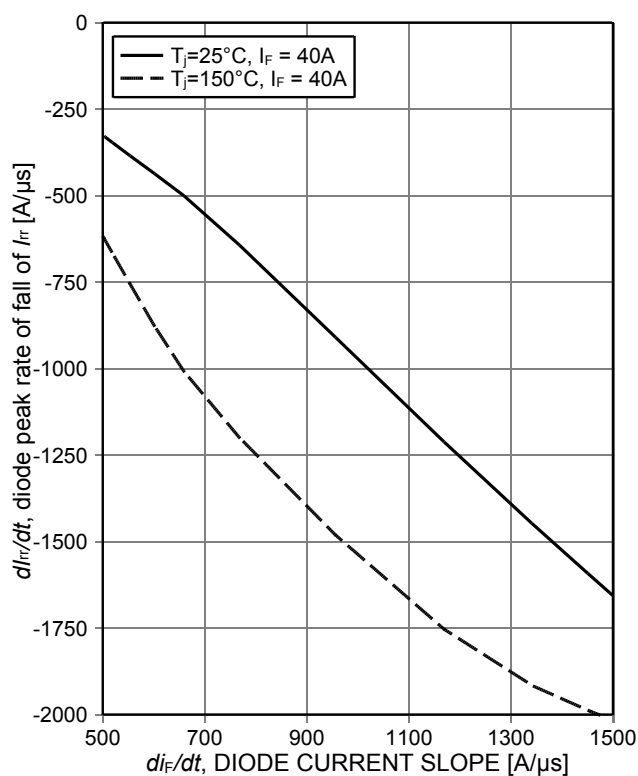


Figure 22. Typical diode peak rate of fall of reverse recovery current as a function of diode current slope ($V_R=400V$)

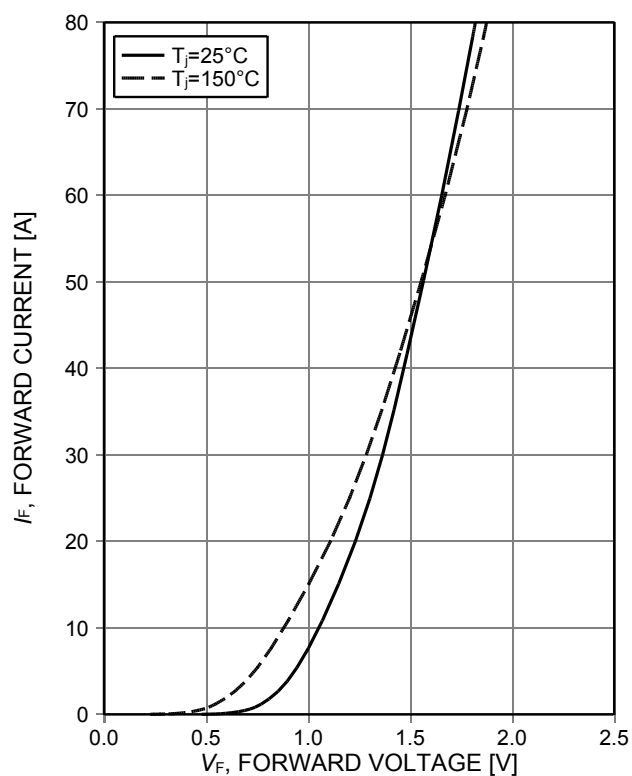


Figure 23. Typical diode forward current as a function of forward voltage

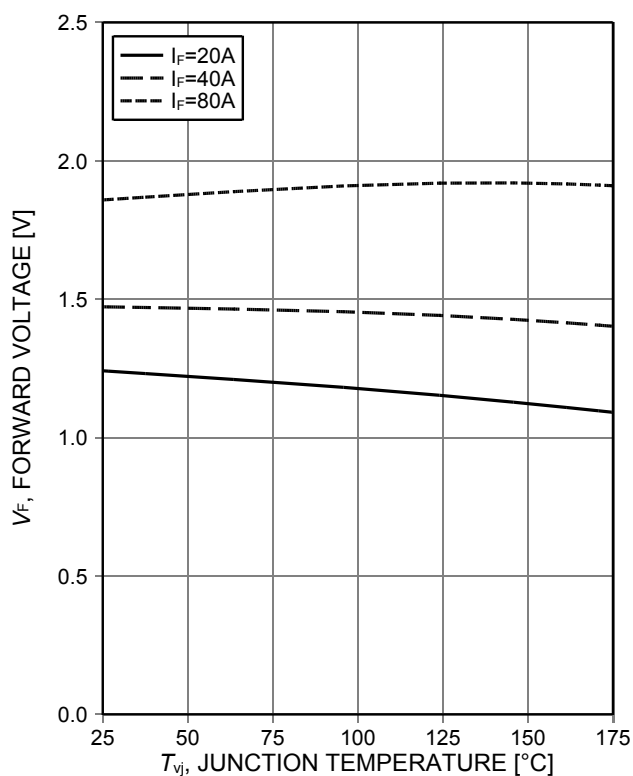
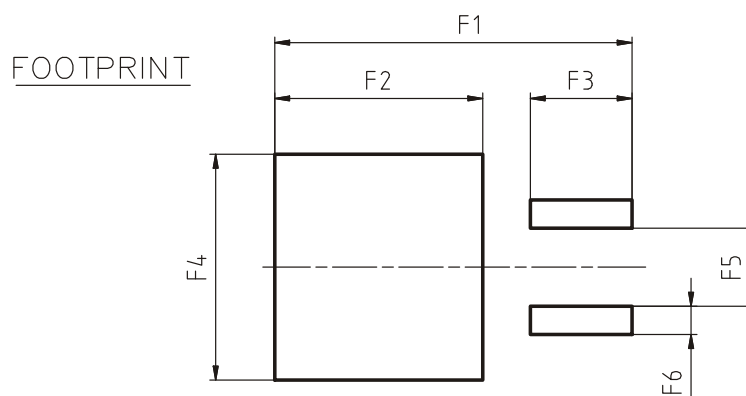
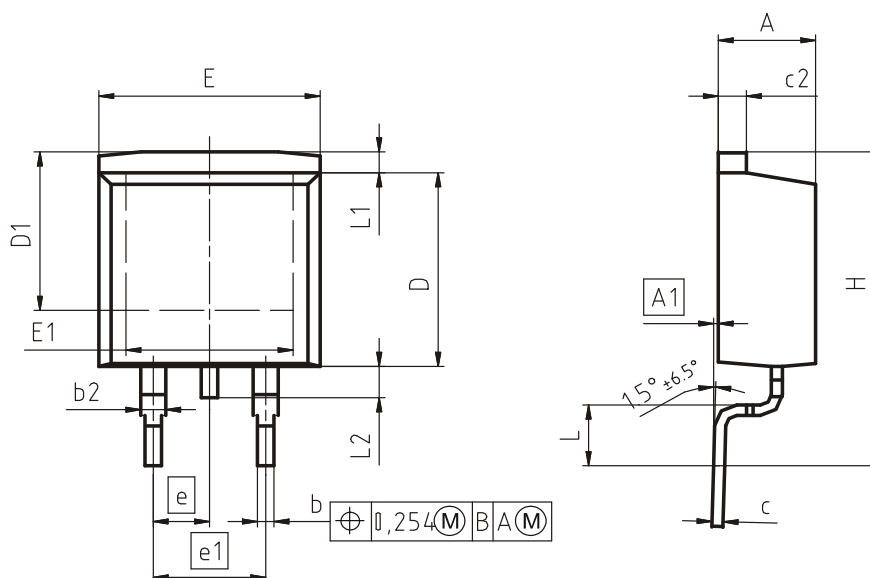


Figure 24. Typical diode forward voltage as a function of junction temperature

Package Drawing PG-TO263-3



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.30	4.57	0.169	0.180
A1	0.00	0.25	0.000	0.010
b	0.65	0.85	0.026	0.033
b2	0.95	1.15	0.037	0.045
c	0.33	0.65	0.013	0.026
c2	1.17	1.40	0.046	0.055
D	8.51	9.45	0.335	0.372
D1	7.10	7.90	0.280	0.311
E	9.80	10.31	0.386	0.406
E1	6.50	8.60	0.256	0.339
e	2.54		0.100	
e1	5.08		0.200	
N	2		2	
H	14.61	15.88	0.575	0.625
L	2.29	3.00	0.090	0.118
L1	0.70	1.60	0.028	0.063
L2	1.00	1.78	0.039	0.070
F1	16.05	16.25	0.632	0.640
F2	9.30	9.50	0.366	0.374
F3	4.50	4.70	0.177	0.185
F4	10.70	10.90	0.421	0.429
F5	3.65	3.85	0.144	0.152
F6	1.25	1.45	0.049	0.057

DOCUMENT NO. Z8B00003324	
SCALE	0 5 5 7.5mm
EUROPEAN PROJECTION	
ISSUE DATE 30-08-2007	
REVISION 01	

Testing Conditions



Figure A. Definition of switching times



Figure B. Definition of switching losses



Figure C. Definition of diode switching characteristics

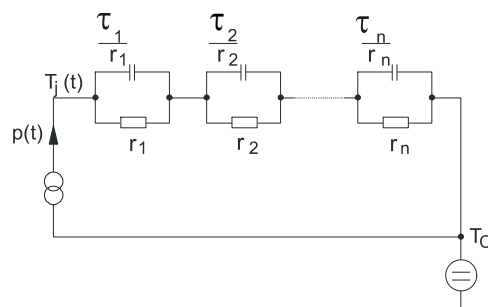


Figure D. Thermal equivalent circuit



Figure E. **Dynamic test circuit**
Parasitic inductance L_σ ,
parasitic capacitor C_σ ,
relief capacitor C_r ,
(only for ZVT switching)

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Revision History

IKB40N65EH5

Revision: 2018-04-04, Rev. 2.1

Previous Revision

Revision	Date	Subjects (major changes since last revision)
2.1	2018-04-04	Final data sheet

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Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

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- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

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